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One Sansome Street Suite 3500 San Francisco CA 94104 Tel 415-954-4114 Fax 415-954-4111 www.kmob.com

## USPTO FACSIMILE TRANSMITTAL SHEET

Page 1 of 1

Docket No.: ASMNUT.124C1

CUSTOMER NO. 20995

Applicant

: Basol et al.

App. No.

10/663,318

Filed

September 16, 2003

For

: CONDUCTIVE STRUCTURE

FABRICATION PROCESS USING NOVEL

LAYERED STRUCTURE AND

CONDUCTIVE STRUCTURE FABRICATED THEREBY FOR USE IN

MULTI-LEVEL METALLIZATION

Examiner

Thao X. Le

Group Art Unit

2814

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I hereby certify that this correspondence and all marked attachments are being transmitted via facsimile to the USPTO Central Fax No. (571) 273-8300 on the date shown below:

December 9, 2005

Adeel S. Akhtar, Reg. No. 11 894

Transmitted herewith for filing and consideration in the above-referenced application are the following items:

- (X) Information Disclosure Statement in 1 pages, including:
  - (X) Form PTO/SB/08 equivalent in 2 pages.
  - (X) 19 references listed.
- (X) Total pages in transmission: 4

The Commissioner is hereby authorized to charge any additional fees which may be required, now or in the future, or credit any overpayment to Account No. 11-1410.

Adeel S. Akhtar

Registration No. 41,394 Attorney of Record Customer No. 20,995

(415) 954-4114

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> Orange County 949-760-0404

San Diego 619-235-8550 Los Angeles 310-551-3450 Riverside 951-781-9231 San Luis Obispo 805-547-5580

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Office on the date shown below:

Docket No.: ASMNUT.124C1

### INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(i)

Applicant

Basol et al.

App. No

10/663,318

Filed

September 16, 2003

For

CONDUCTIVE STRUCTURE

FABRICATION PROCESS USING NOVEL LAYERED STRUCTURE AND CONDUCTIVE STRUCTURE FABRICATED THEREBY FOR USE

IN MULTI-LEVEL METALLIZATION

Examiner

Thao X. Le

Art Unit

2814

### Mail Stop Amendment

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Enclosed is a PTO/SB/08 Equivalent listing 19 references that are of record in U.S. patent application No. 09/642,827, filed August 22, 2000, which is the parent of this continuation application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. Copies of the references are not submitted pursuant to 37 C.F.R. § 1.98(d).

Pursuant to MPEP § 609.02A.2, since these references were cited in the parent application, Applicants presume that the references have already been considered and that the present submission is unnecessary. However, Applicants submit the listing simply to complete the file.

This Information Disclosure Statement is being filed after the mailing date of a final action or after the mailing date of a Notice of Allowance. Please place these references in the file of the above-identified patent application in accordance with 37 C.F.R. § 1.97(i).

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: 1>ecember 9,2005

Adeel S. Akhtar Registration No. 41,394

Attorney of Record Customer No. 20,995

(415) 954-4114

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PTO/SB/08 Equivalent

		PTO/SB/08 Equivalent
	Application No.	10/663,318
INFORMATION DISCLOSURE	Filing Date	September 16, 2003
STATEMENT BY APPLICANT	First Named Inventor	Basol et al.
STATEMENT BY APPLICANT	Art Unit	2814
(Multiple sheets used when necessary)	Examiner	Thao X Le
SHEET 1 OF 2	Attorney Docket No.	ASMNUT.124C1

			U.S. PATENT	DOCUMENTS	
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pagas, Columns, Lines Where Relevant Passages or Relevant Figures Appear
	1	4,475,983	10-1984	Bader et al.	
	2	5,084,412	01-1992	Nakasaki	
	3	5,939,788	08-1999	McTeer	
	4	6,040,240	03-2000	Matsubara	
	5	6,043,153	03-2000	Nogami et al.	
	6	6,071,388	06-2000	Uzoh	
	7	6,103,624	08-2000	Nogami et al.	
	8	6,132,587	10-2000	Jome et al.	
	9	6,204,179	03-2001	McTeer	
	10	6,278,153	08-2001	Kikichi et al.	
	11	6,326,303	12-2001	Robinson et al.	
	12	6,326,692	12-2001	Pangrie et al.	
	13	6,452,274	09-2002	Hasagawa et al.	
	14	2002/0001941 A1	01-2002	Kudo	

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T <sup>1</sup>

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Т1
	15	BRAUN, A., "ECP technology faces chemical, dielectric hurdles," <u>Cahners Semiconductor</u> International, May 2, 2000, pp. 1-9.	

Examiner	Signature
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Date Considered

\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

T¹ - Place a check mark in this area when an English language Translation is attached.

PTO/SB/08 Equivalent Application No. 10/663,318 INFORMATION DISCLOSURE Filing Date September 16, 2003 First Named Inventor Basol et al. STATEMENT BY APPLICANT **Art Unit** 2814 (Multiple sheets used when necessary) Examiner Thao X Le SHEET 2 OF 2 Attorney Docket No. ASMNUT.124C1

	NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	т'	
	16	JIN et al., "Nanoporous silica as an ultralow-k dielectric," MRS Bulletin, October 1997, pp. 39-42.		
	17	LEE et al., "Low-dielectric-constant materials for ULSI interlayer-dielectric applications," MRS Bulletin, October 1997, pp. 19-23.		
	18	MONNIG, K., "Why copper and low K?," Future Fab, May 3, 1989, Issue 5, pp. 1-7,		
	19	International Preliminary Examination Report generated in connection with corresponding international application PCT/US00/42575.		

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